SM05T1G Series, SZSM05T1G

Transient Voltage Suppressor Diode Array

SOT−23 Dual Common Anode Diodes for ESD Protection

These dual monolithic silicon TVS diodes are designed for applications requiring transient overvoltage protection capability. They are intended for use in voltage and ESD sensitive equipment such as computers, printers, business machines, communication systems, medical equipment and other applications. Their dual junction common anode design protects two separate lines using only one package. These devices are ideal for situations where board space is at a premium.

Specification Features:

- SOT−23 Package Allows Either Two Separate Unidirectional Configurations or a Single Bidirectional Configuration
- Working Peak Reverse Voltage Range − 5.0 V to 24 V
- Peak Power − 300 Watt (8 X 20 μs)
- Low Leakage
- Flammability Rating UL 94 V−0
- SZ Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC−Q101 Qualified and PPAP Capable
- These are Pb−Free Devices

Mechanical Characteristics:

CASE: Void-Free, Transfer-Molded, Thermosetting Plastic Case
FINISH: Corrosion Resistant Finish, Easily Solderable
MAXIMUM CASE TEMPERATURE FOR SOLDERING PURPOSES: 260°C for 10 Seconds
Package Designed for Optimal Automated Board Assembly
Small Package Size for High Density Applications
Available in 8 mm Tape and Reel
Use the Device Number to Order the 7 Inch/3,000 Unit Reel
Replace the “T1” with “T3” in the Device Number to Order the 13 Inch/10,000 Unit Reel

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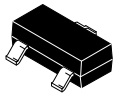
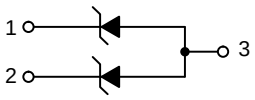
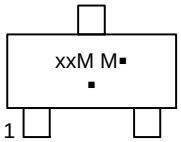


SOT−23
CASE 318
STYLE 12



PIN 1. CATHODE
2. CATHODE
3. ANODE

MARKING DIAGRAM



xxM = Device Code
xx = 05, 12, 15, 24, 36
M = Date Code*
▪ = Pb−Free Package

(Note: Microdot may be in either location)

*Date Code orientation and/or overbar may vary depending upon manufacturing location.

ORDERING INFORMATION

Device	Package	Shipping†
SM05T1G	SOT−23 (Pb−Free)	3,000/Tape & Reel
SZSM05T1G	SOT−23 (Pb−Free)	3,000/Tape & Reel
SM12T1G	SOT−23 (Pb−Free)	3,000/Tape & Reel
SM15T1G	SOT−23 (Pb−Free)	3,000/Tape & Reel
SM24T1G	SOT−23 (Pb−Free)	3,000/Tape & Reel
SM36T1G	SOT−23 (Pb−Free)	3,000/Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

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MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Peak Power Dissipation @ 20 μs (Note 1) @ $T_L \le 25°C$	P_{pk}	300	W
IEC 61000−4−2 (ESD) Air Contact		 ±15 ±8.0	kV
IEC 61000−4−4 (EFT)		40	A
IEC 61000−4−5 (Lightening)		12	A
Total Power Dissipation on FR−5 Board (Note 2) @ $T_A = 25°C$ Derate above 25°C Thermal Resistance, Junction−to−Ambient	P_D $R_{\theta JA}$	225 1.8 556	mW mW/°C °C/W
Total Power Dissipation on Alumina Substrate (Note 3) @ $T_A = 25°C$ Derate above 25°C Thermal Resistance, Junction−to−Ambient	P_D $R_{\theta JA}$	300 2.4 417	mW mW/°C °C/W
Junction and Storage Temperature Range	T_J, T_{stg}	− 55 to +150	°C
Lead Solder Temperature − Maximum (10 Second Duration)	T_L	260	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

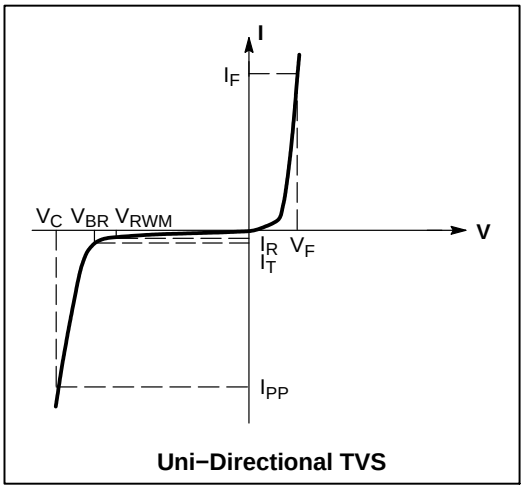
1. Non−repetitive current pulse per Figure 3
2. FR−5 = 1.0 x 0.75 x 0.62 in.
3. Alumina = 0.4 x 0.3 x 0.024 in., 99.5% alumina

NOTE: Other voltages may be available upon request

ELECTRICAL CHARACTERISTICS

UNIDIRECTIONAL (Circuit tied to Pins 1 and 3 or 2 and 3)

Symbol	Parameter
I_{PP}	Maximum Reverse Peak Pulse Current
V_C	Clamping Voltage @ I_{PP}
V_{RWM}	Working Peak Reverse Voltage
I_R	Maximum Reverse Leakage Current @ V_{RWM}
V_{BR}	Breakdown Voltage @ I_T
I_T	Test Current
ΘV_{BR}	Maximum Temperature Coefficient of V_{BR}
I_F	Forward Current
V_F	Forward Voltage @ I_F
Z_{ZT}	Maximum Zener Impedance @ I_{ZT}
I_{ZK}	Reverse Current
Z_{ZK}	Maximum Zener Impedance @ I_{ZK}



Uni−Directional TVS

ELECTRICAL CHARACTERISTICS ($T_A = 25°C$ unless otherwise noted)

Device*	Device Marking	V_{RWM} (Volts)	I_R @ V_{RWM} (μA)	V_{BR}, Breakdown Voltage (Volts) Min	V_{BR}, Breakdown Voltage (Volts) Max	I_T mA	V_C @ I_{PP} = 1 Amp (Volts)	Max I_{PP} (Note 4) (Amps)	Typical Capacitance (pF) Pin 1 to 3 @ 0 Volts
SM05T1G	05M	5	10	6.2	7.3	1.0	9.8	17	225
SM12T1G	12M	12	1.0	13.3	15.75	1.0	19	12	95
SM15T1G	15M	15	1.0	16.7	19.6	1.0	24	10	100
SM24T1G	24M	24	1.0	26.7	31.35	1.0	43	5.0	60
SM36T1G	36M	36	1.0	40.0	46.95	1.0	60	4.0	45

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

4. 8 × 20 μs pulse waveform per Figure 3

*Include SZ-prefix devices where applicable.

TYPICAL CHARACTERISTICS

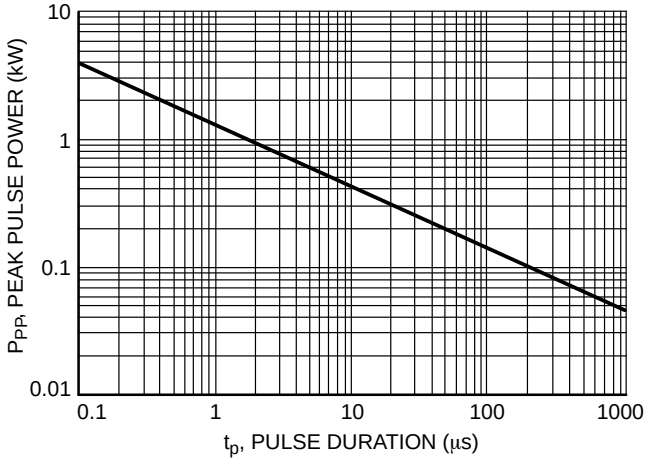


Figure 1. Non−Repetitive Peak Pulse Power versus Pulse Time

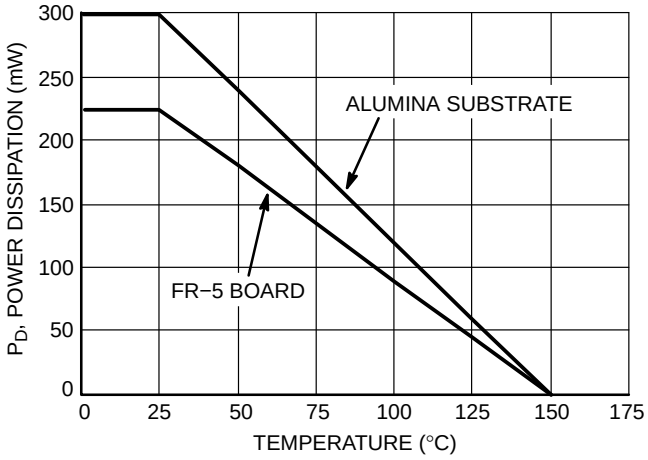


Figure 2. Steady State Power Derating Curve

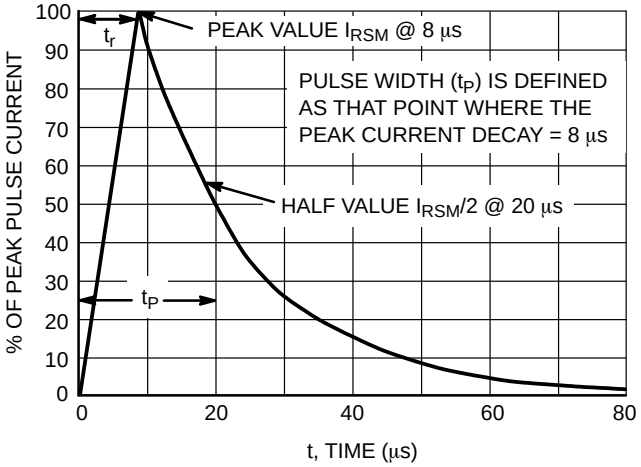


Figure 3. 8 × 20 μs Pulse Waveform

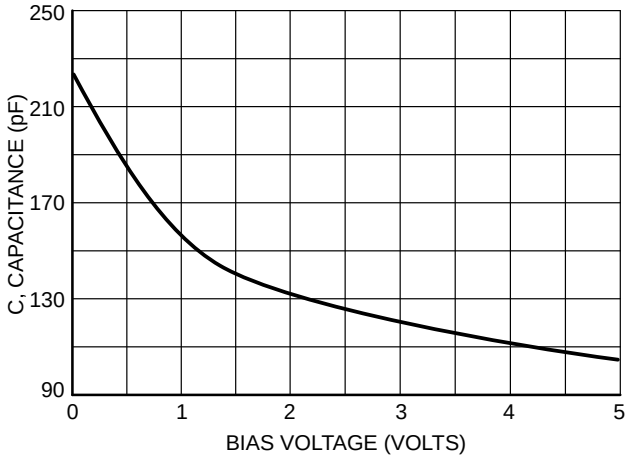


Figure 4. Typical Diode Capacitance (SM05)

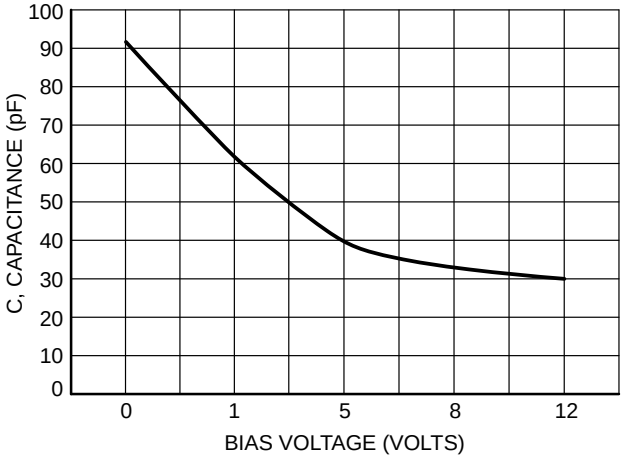
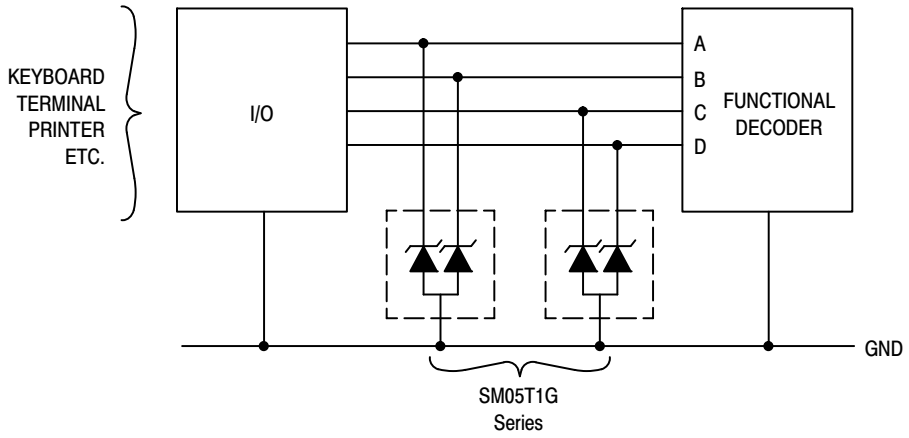


Figure 5. Typical Diode Capacitance (SM12)

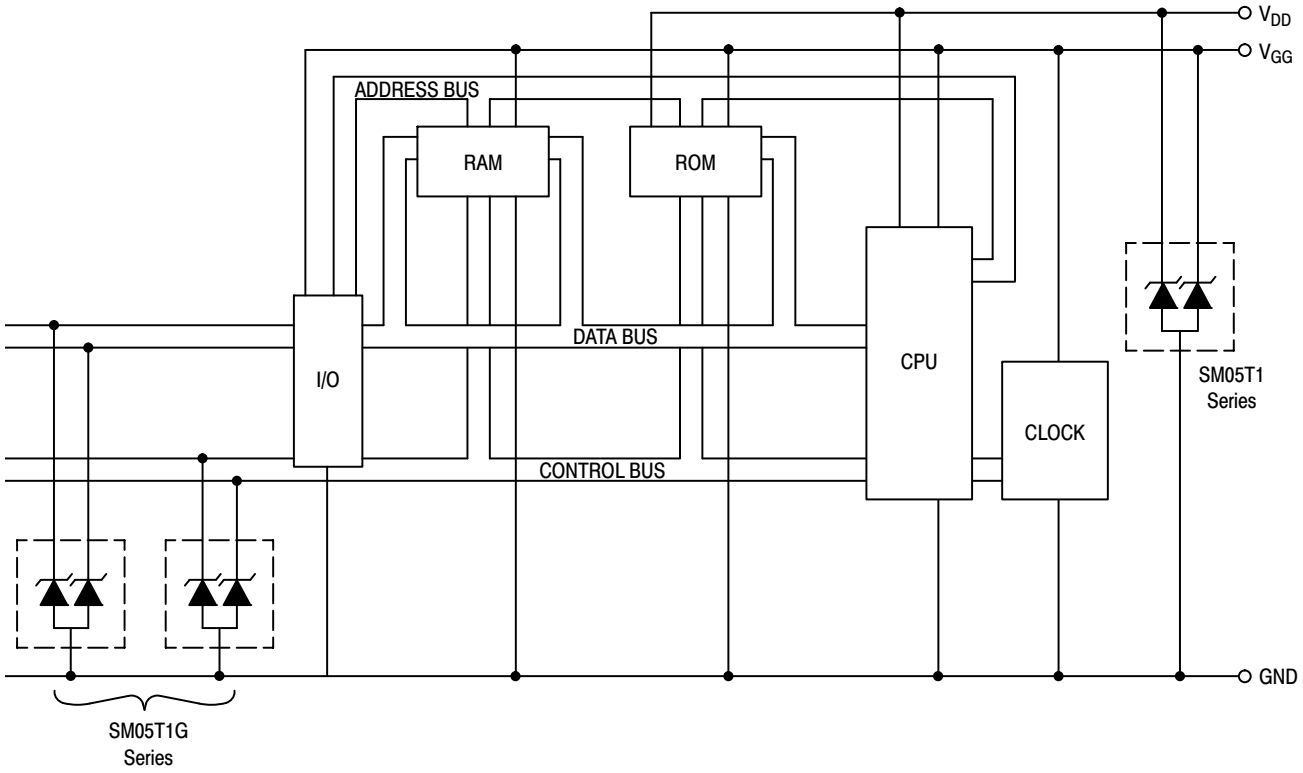
TYPICAL COMMON ANODE APPLICATIONS

A quad junction common anode design in a SOT−23 package protects four separate lines using only one package. This adds flexibility and creativity to PCB design especially when board space is at a premium. Two simplified examples of TVS applications are illustrated below.

Computer Interface Protection

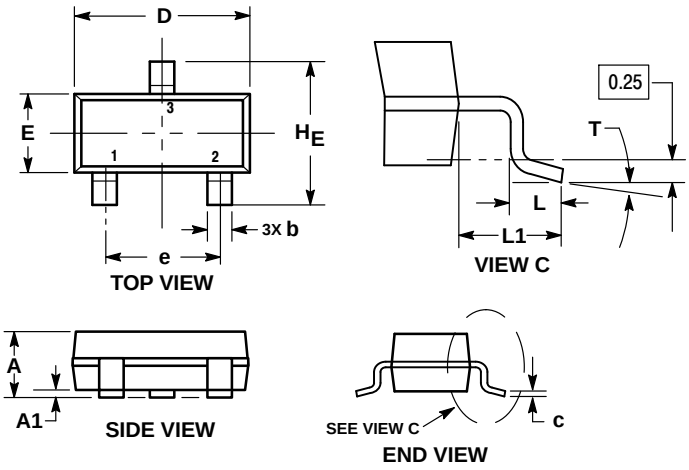


Microprocessor Protection



PACKAGE DIMENSIONS

SOT−23 (TO−236)
CASE 318−08
ISSUE AR

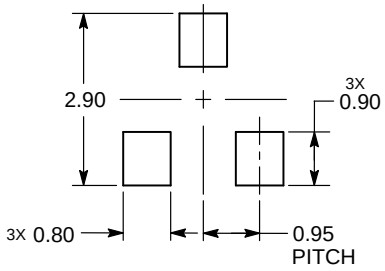


NOTES:
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF THE BASE MATERIAL.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

	MILLIMETERS			INCHES		
DIM	MIN	NOM	MAX	MIN	NOM	MAX
A	0.89	1.00	1.11	0.035	0.039	0.044
A1	0.01	0.06	0.10	0.000	0.002	0.004
b	0.37	0.44	0.50	0.015	0.017	0.020
c	0.08	0.14	0.20	0.003	0.006	0.008
D	2.80	2.90	3.04	0.110	0.114	0.120
E	1.20	1.30	1.40	0.047	0.051	0.055
e	1.78	1.90	2.04	0.070	0.075	0.080
L	0.30	0.43	0.55	0.012	0.017	0.022
L1	0.35	0.54	0.69	0.014	0.021	0.027
H_E	2.10	2.40	2.64	0.083	0.094	0.104
T	0°	−−−	10°	0°	−−−	10°

STYLE 12:
PIN 1. CATHODE
2. CATHODE
3. ANODE

RECOMMENDED SOLDERING FOOTPRINT*



DIMENSIONS: MILLIMETERS

*For additional information on our Pb−Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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